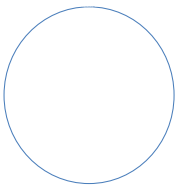
100V N-Ch Power MOSFET

V_{DS}		100	V
$R_{DS(on),typ}$	V_{GS}=10V	4.9	m :
$R_{DS(on),typ}$	V_{GS}=4.5V	5.8	m :
I_D		62.7	A



Part Number	Package	Marking
HGA055N10SL	TO-220F	GA055N10SL

Absolute Maximum Ratings at T_j=25 (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current	I_D	T_C=25	63	A
		T_C=100	44	
Drain to Source Voltage	V_{DS}	-	100	V
Gate to Source Voltage	V_{GS}	-	±20	V
Pulsed Drain Current	I_{DM}	-	350	A
Avalanche Energy, Single Pulse	E_{AS}	L=0.3mH, T_C=25	240	mJ
Power Dissipation	P_D	T_C=25	43	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to175	

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Case	R æJC	3.5	/W
Thermal Resistance Junction-Ambient	R æJA	50	/W

Fig 1

Figu

Figure 5. Typical Transfer Characteristics	Figure 6. Typical Source-Drain Diode Forward Voltage

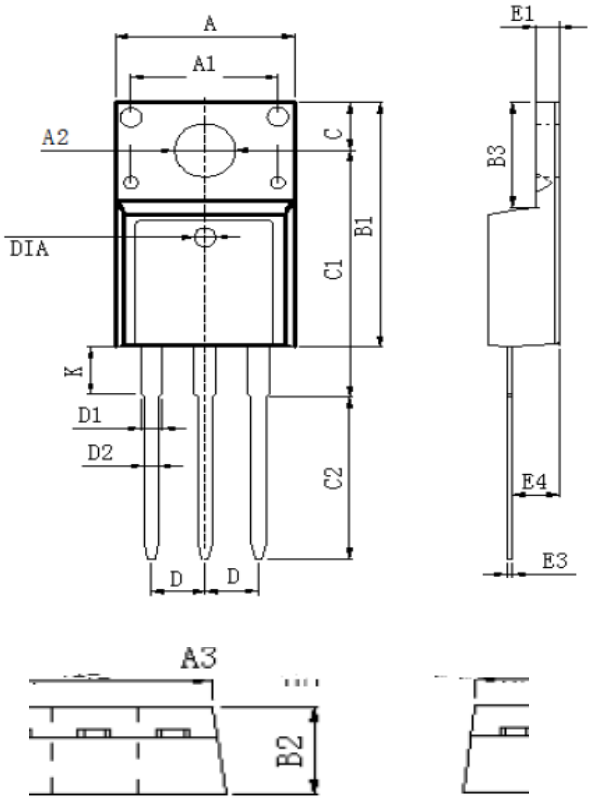
Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage	Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

Figure 9. Maximum Safe Operating Area	Figure 10. Maximun Drain Current vs. Case Temperature

Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Case

Package Outline

TO-220F, 3 leads



DIM	MILLIMETERS
A	10.16±0.3
A1	7.00±0.1
A2	3.3±0.2
A3	9.5±0.2
B1	15.85±0.3
B2	4.7±0.2
B3	6.68±0.4
C	3.3±0.2
C1	12.57±0.3
C2	10.02±0.5
D	2.54±0.05
D1	1.28±0.2
D2	0.8±0.1
K	3.1±0.3
E1	[illegible]
.5±0.1	E3 0
.76±0.2	[illegible]
5(deep 0.2)	DIA ⊙1.
Unit :mm	